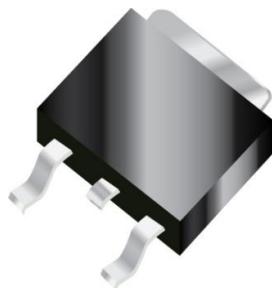




ESIC0506SD

RoHS Pb

Silicon carbide power schottky diode



D2-PAK



Features		
• 600-Volt Schottky Rectifier		
• Zero Reverse Recovery Current		
• Zero Forward Recovery Voltage		
• High-Frequency Operation		
• Temperature-Independent Switching Behavior		
• Extremely Fast Switching		
• Positive Temperature Coefficient on VF		
• Marking : ESIC0506SD		

Ordering Information		
Part No.	Package	Packing
ESIC0506SD	D2-PAK	2500/ Tape & Reel

Benefits		
• Replace Bipolar with Unipolar Rectifiers		
• Essentially No Switching Losses		
• Higher Efficiency		
• Reduction of Heat Sink Requirements		
• Parallel Devices Without Thermal Runaway		

Application		
• Switching power supply		
• Solar inverter		
• Uninterruptible power supply		
• Power factor correction		
• Motor drive		

Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)					
Parameter	Conditions	Symbol	Limits	Unit	
Repetitive Peak Reverse Voltage	$T_j=25^\circ\text{C}$	$V_{RRM}$	600	V	
Surge Peak Reverse Voltage	$T_j=25^\circ\text{C}$	$V_{RSM}$	600	V	
DC Blocking Voltage	$T_j=25^\circ\text{C}$	$V_{DC}$	600	V	
Continuous Forward Current	$T_j=150^\circ\text{C}$	$I_F$	5	A	
Repetitive Peak Forward Surge Current	$T_C=25^\circ\text{C}$ , tp=10ms, Half Sine Wave, D=0.3	$I_{FRM}$	45	A	
Non-Repetitive Peak Forward Surge Current	$T_C=25^\circ\text{C}$ , tp=10ms, Half Sine Wave, D=0.3	$I_{FSM}$	75	A	
Power Dissipation	$T_C=25^\circ\text{C}$	$P_{TOT}$	90	W	
	$T_C=110^\circ\text{C}$		39	W	
Reverse recovery time	$I_F=5\text{A}, di/dt=200\text{A}/\mu\text{s}$	$T_{rr}$	10	ns	
Operating Junction and Storage Temperature		$T_j$ 、 $T_{stg}$	-55~+175	$^\circ\text{C}$	
Typical Thermal Resistance form Junction to Case		$R_{\theta JC}$	1.67	$^\circ\text{C}/\text{W}$	

Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise specified)						
Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage	$I_F=5\text{A}, T_j=25^\circ\text{C}$	$V_F$	-	1.35	1.8	V
	$I_F=5\text{A}, T_j=175^\circ\text{C}$		-	1.75	2.4	
Reverse Current	$V_R=600\text{V}, T_j=25^\circ\text{C}$	$I_R$	-	7.1	100	$\mu\text{A}$
	$V_R=600\text{V}, T_j=175^\circ\text{C}$		-	15	200	
Total Capacitive Charge	$V_R=600\text{V}, I_F=5\text{A}, di/dt=500\text{A}/\mu\text{s}, T_j=25^\circ\text{C}$	$Q_C$	-	15	-	$\mu\text{A}$
	$V_R=0\text{V}, T_j=25^\circ\text{C}, f=1\text{MHz}$		-	230	-	
Total Capacitive Charge	$V_R=200\text{V}, T_j=25^\circ\text{C}, f=1\text{MHz}$	$C$	-	32	-	$\mu\text{A}$
	$V_R=400\text{V}, T_j=25^\circ\text{C}, f=1\text{MHz}$		-	30	-	



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### Rating and Characteristics Curves

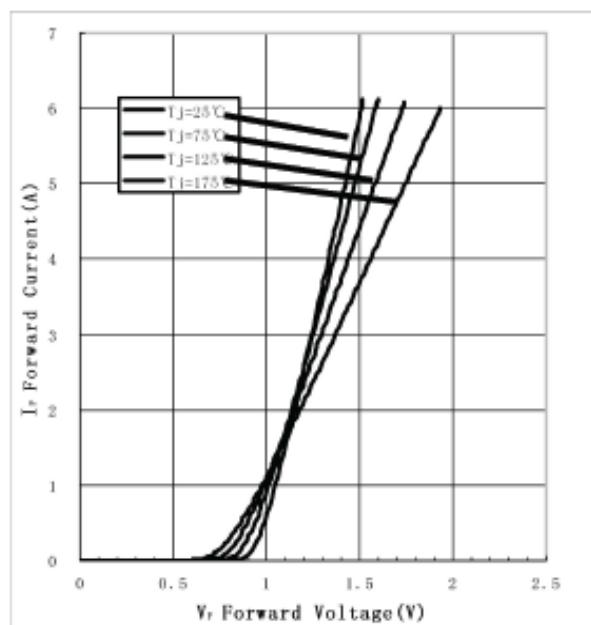


Figure 1. Forward Characteristics

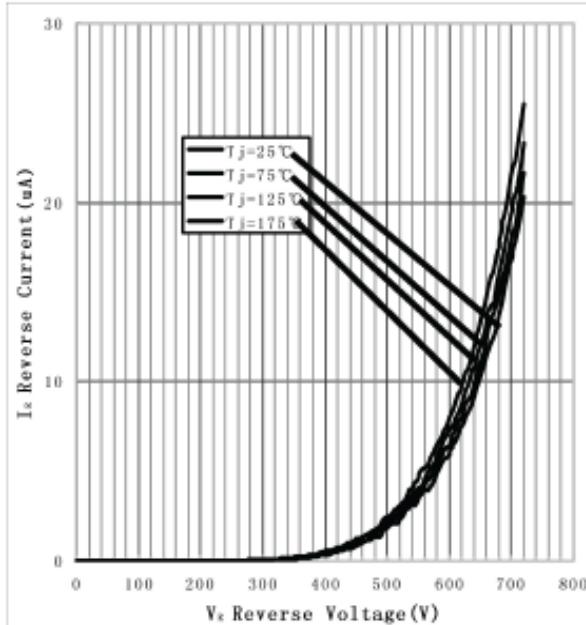


Figure 2. Reverse Characteristics

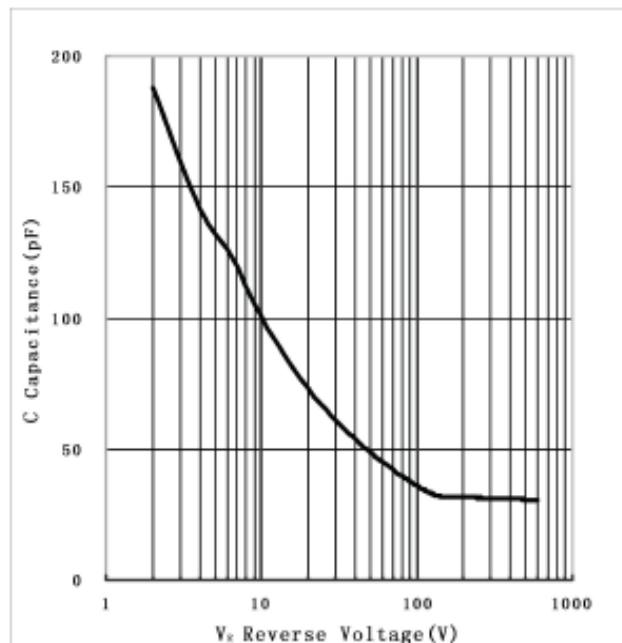


Figure 4. Power Derating

